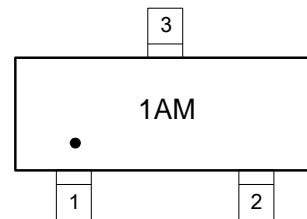


WNT2F04
NPN, General Purpose Transistors
[Http://www.willsemi.com](http://www.willsemi.com)
Descriptions

The WNT2F04 is designed for general purpose amplifier applications. Standard products are Pb-free and Halogen-free


SOT-23
Features

- Complementary to WPT2F06
- Collector Current: $I_c=0.2A$

(Top View)

Marking :1AM

- 1: BASE**
- 2: EMITTER**
- 3: COLLECTOR**

Order information

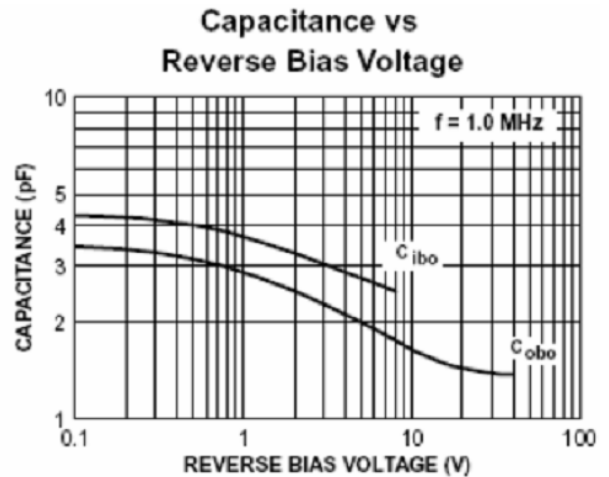
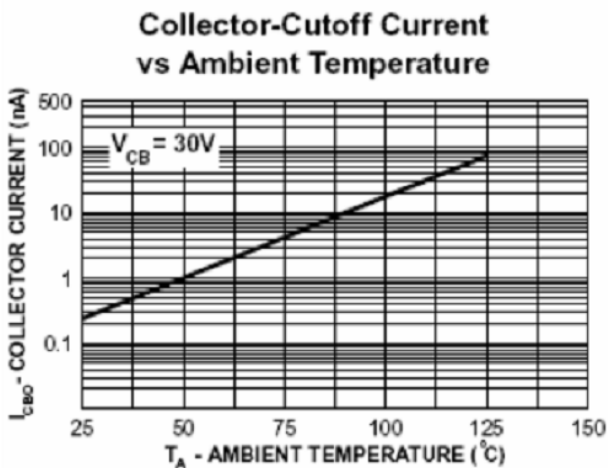
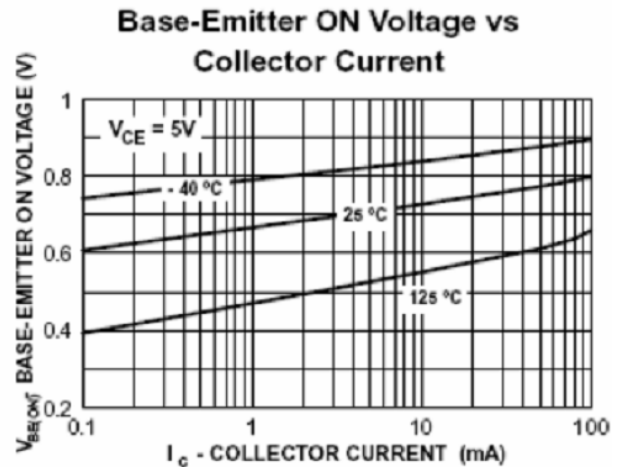
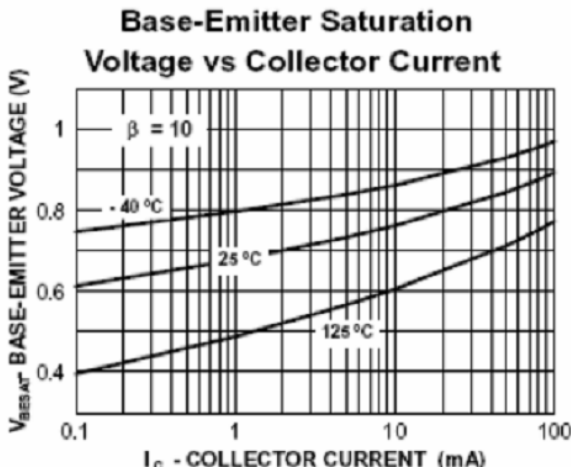
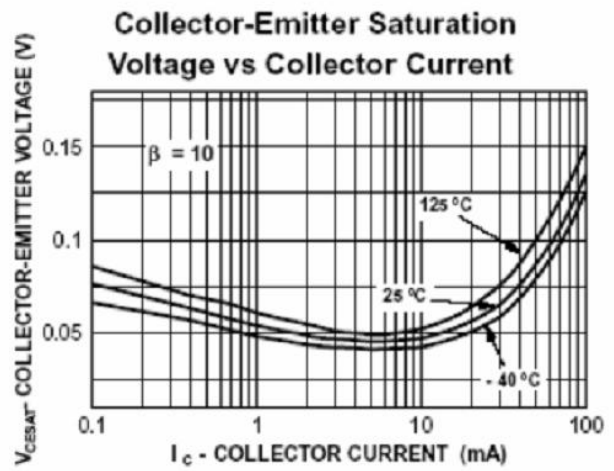
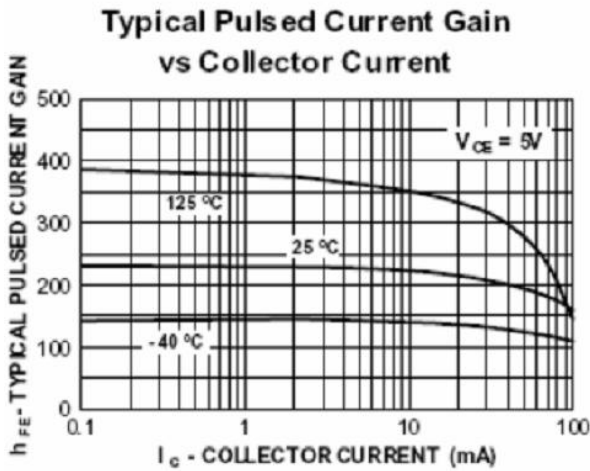
Device	Package	Shipping
WNT2F04-3/TR	SOT-23	3000/Reel&Tape

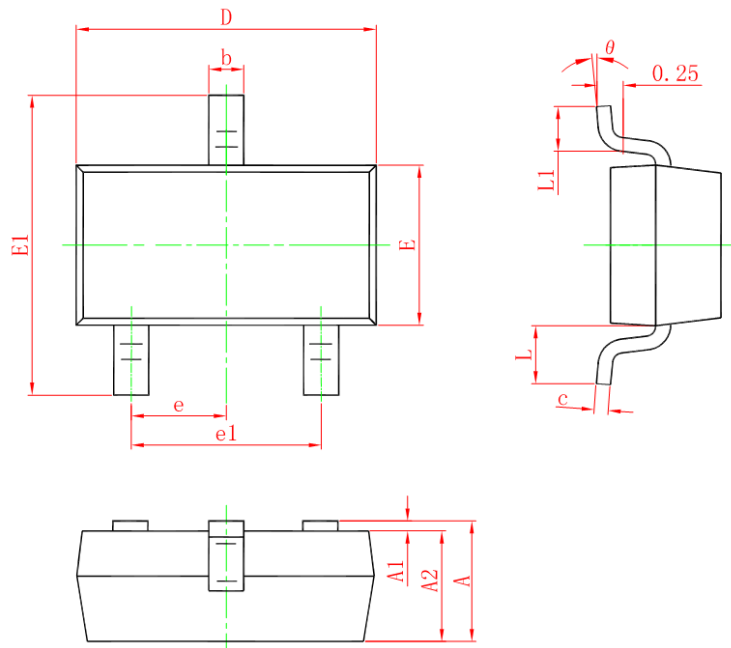
Absolute maximum ratings

Parameter	Symbol	Value	Unit
Collector-emitter Voltage	V_{CEO}	40	V
Collector-base Voltage	V_{CBO}	60	V
Emitter-base Voltage	V_{EBO}	6	V
Continues Collector Current	I_C	200	mA
Collector Power Dissipation	P_C	250	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	625	$^{\circ}C /W$
Junction Temperature	T_J	150	$^{\circ}C$
Operating Temperature	T_{OPR}	0~+70	$^{\circ}C$
Storage Temperature Range	T_{stg}	-55~+150	$^{\circ}C$

Electronics Characteristics ($T_a=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Max.	Unit
Collector-emitter breakdown voltage	BV_{CEO}	$I_C=1\text{mA}, I_B=0\text{mA}$	40		V
Collector-base breakdown voltage	BV_{CBO}	$I_C=10\mu\text{A}, I_E=0\text{mA}$	60		V
Emitter-base breakdown voltage	BV_{EBO}	$I_E=10\mu\text{A}, I_C=0\text{mA}$	6		V
Collector cutoff current	I_{CEX}	$V_{CE}=30\text{V},$ $V_{EB(OFF)}=3\text{V}$		50	nA
Collector cutoff current	I_{CBO}	$V_{CB}=60\text{V}, I_E=0\text{A}$		100	nA
Emitter cutoff current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0\text{A}$		100	nA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50\text{mA}, I_B=5\text{mA}$		0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=50\text{mA}, I_B=5\text{mA}$		0.95	V
DC current gain	h_{FE}	$V_{CE}=1\text{V}, I_C=1\text{mA}$	80		
		$V_{CE}=1\text{V}, I_C=10\text{mA}$	100	300	
		$V_{CE}=1\text{V}, I_C=50\text{mA}$	60		
Collector capacitance	C_C	$I_E=I_C=0; V_{CE}=5\text{V};$ $f=1\text{MHz}$		4	pF
Emitter capacitance	C_E	$I_C=I_C=0; V_{BE}=0.5\text{V};$ $f=1\text{MHz}$		8	pF
Noise figure	F	$I_C=100\text{mA};$ $V_{CE}=5\text{V}; R_S=1\text{k}\Omega;$ $f=10\text{Hz to }15.7\text{kHz}$		5	dB
Transition frequency	f_T	$V_{CE}=20\text{V},$ $I_C=10\text{mA},$ $f=100\text{MHz}$	300		MHz
Delay time	t_d	$V_{CC}=3\text{V},$ $V_{BE(off)}=-0.5\text{V}$ $I_C=10\text{mA},$ $I_{B1}=1\text{mA}$		35	ns
Rise time	t_r			35	ns
Storage time	t_s			200	ns
Fall time	t_f		$I_{B1}= I_{B2}=1\text{mA}$		50

Typical characteristics ($T_a=25^\circ\text{C}$, unless otherwise noted)


Package outline dimensions
SOT-23


Symbol	Dimensions in millimeter		
	Min.	Typ.	Max.
A	0.900	1.025	1.150
A1	0.000	0.500	0.100
A2	0.900	0.975	1.050
b	0.300	0.400	0.500
c	0.080	0.115	0.150
D	2.800	2.900	3.000
E	1.200	1.300	1.400
E1	2.250	2.400	2.550
e	0.950TYP		
e1	1.800	1.900	2.000
L	0.500REF		
L1	0.300	0.400	0.500
θ	0°	4°	8°

Recommend PCB Layout (Unit: mm)
